Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	40	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1.5	kV

ELECTRICAL CHARACTERISTICS(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j=125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	-	MAX.	80	mA
				200	
I_H	I_T =500mA		MAX.	100	mA
dV/dt	V_D=540V Gate Open T_j=125		MIN.	2000	V/μs
(dI/dt)c	(dV/dt)c=20V/μs T_j=125		MIN.	25	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS

Symbol

FIG.1: Maximum power dissipation versus RMS on-state current

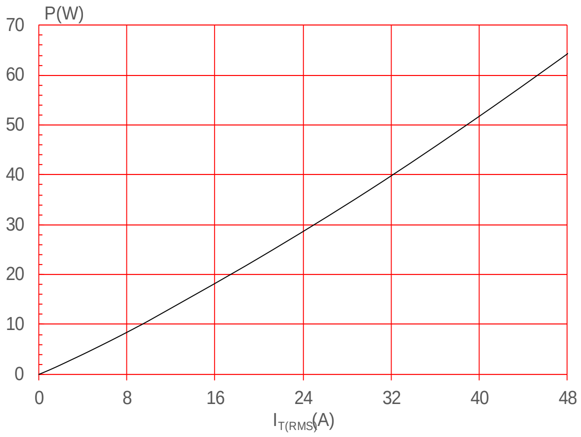

FIG.2: RMS on-state current versus case temperature

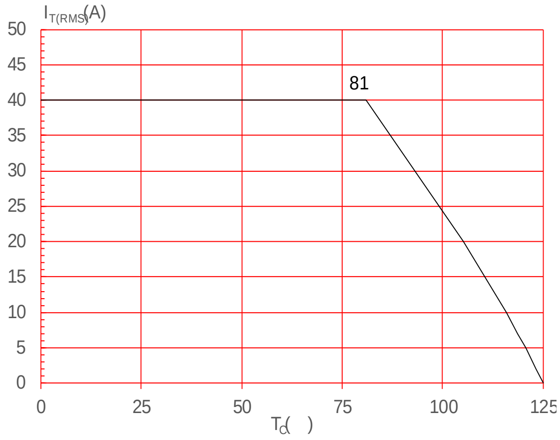

FIG.3: Surge peak on-state current versus number of cycles

FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-

ORDERING INFORMATION

Order code	**Voltage V_{DRM}/V_{RRM}(V)**	**IGT(mA)**	**Package**	**Base qty. (pcs)**	**Delivery mode**
		- -			
JST41Z-800BW	**800**	**50**	**TO-3P(Ins)**	**30**	**Tube**

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA

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